



SANYO Semiconductors

DATA SHEET

An ON Semiconductor Company

N-Channel Silicon MOSFET

BMS4007 — General-Purpose Switching Device Applications

Features

- ON-resistance $R_{DS(on)}=6\text{m}\Omega$ (typ.)
- Input capacitance $C_{iss}=9700\text{pF}$ (typ.)
- 10V drive

Specifications

Absolute Maximum Ratings at $T_a=25^\circ\text{C}$

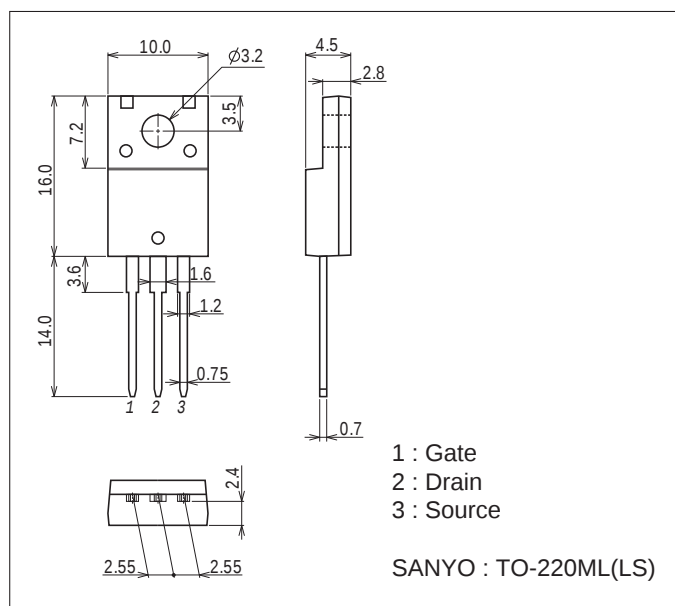
Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V_{DS}		75	V
Gate-to-Source Voltage	V_{GS}		± 20	V
Drain Current (DC)	I_D		60	A
Drain Current (Pulse)	I_{DP}	$PW \leq 10\mu\text{s}$, duty cycle $\leq 1\%$	240	A
Allowable Power Dissipation	P_D		2.0	W
		$T_c=25^\circ\text{C}$	30	W
Channel Temperature	T_{ch}		150	$^\circ\text{C}$
Storage Temperature	T_{stg}		-55 to $+150$	$^\circ\text{C}$
Avalanche Energy (Single Pulse) *1	E_{AS}		299	mJ
Avalanche Current *2	I_{AV}		48	A

Note : *1 $V_{DD}=48\text{V}$, $L=100\mu\text{H}$, $I_{AV}=48\text{A}$ (Fig.1)*2 $L \leq 100\mu\text{H}$, Single pulse

Package Dimensions

unit : mm (typ)

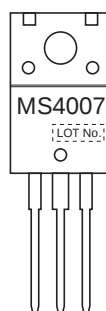
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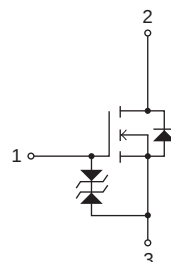
Product & Package Information

- Package : TO-220ML(LS)
- JEITA, JEDEC : SC-67, SOT-186A
- Minimum Packing Quantity : 100 pcs./bag or 50pcs./magazine

Marking



Electrical Connection



Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	$V_{(BR)DSS}$	$I_D=1mA, V_{GS}=0V$	75			V
Zero-Gate Voltage Drain Current	I_{DSS}	$V_{DS}=75V, V_{GS}=0V$			10	μA
Gate-to-Source Leakage Current	I_{GSS}	$V_{GS}=\pm 16V, V_{DS}=0V$			± 10	μA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS}=10V, I_D=1mA$	2		4	V
Forward Transfer Admittance	$ y_{fs} $	$V_{DS}=10V, I_D=30A$		110		S
Static Drain-to-Source On-State Resistance	$R_{DS(on)}$	$I_D=30A, V_{GS}=10V$		6	7.8	$m\Omega$
Input Capacitance	C_{iss}	$V_{DS}=20V, f=1MHz$		9700		pF
Output Capacitance	C_{oss}			540		pF
Reverse Transfer Capacitance	C_{rss}			360		pF
Turn-ON Delay Time	$t_{d(on)}$			100		ns
Rise Time	t_r	See Fig.2		180		ns
Turn-OFF Delay Time	$t_{d(off)}$			460		ns
Fall Time	t_f			160		ns
Total Gate Charge	Q_g	$V_{DS}=48V, V_{GS}=10V, I_D=60A$		160		nC
Gate-to-Source Charge	Q_{gs}			40		nC
Gate-to-Drain "Miller" Charge	Q_{gd}			40		nC
Diode Forward Voltage	V_{SD}	$I_S=60A, V_{GS}=0V$		0.9	1.2	V
Reverse Recovery Time	t_{rr}	See Fig.3		70		ns
Reverse Recovery Charge	Q_{rr}			183		nC

Fig.1 Avalanche Resistance Test Circuit

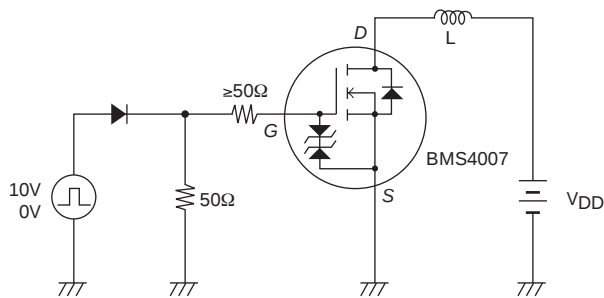


Fig.2 Switching Time Test Circuit

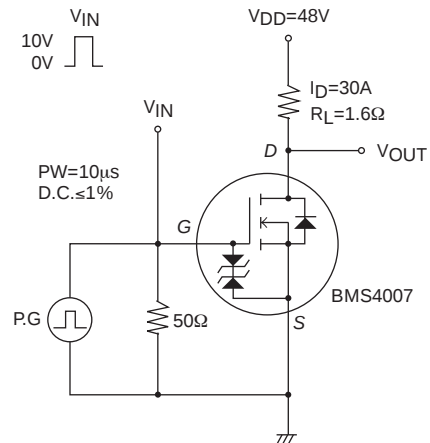
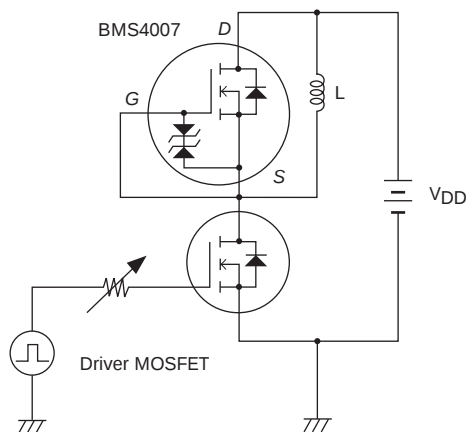
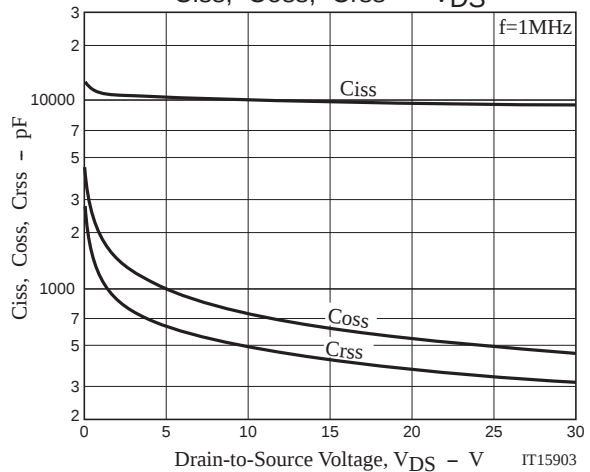
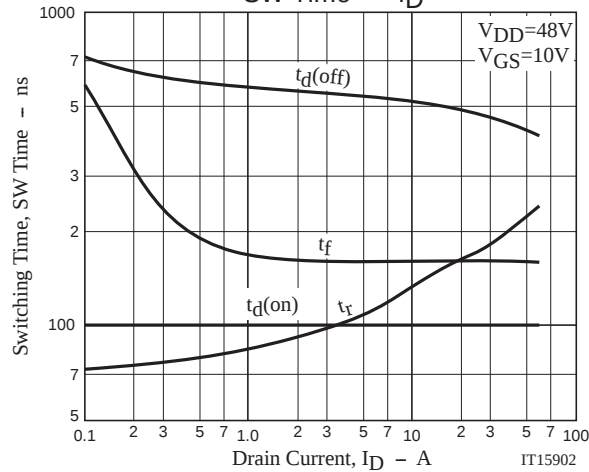
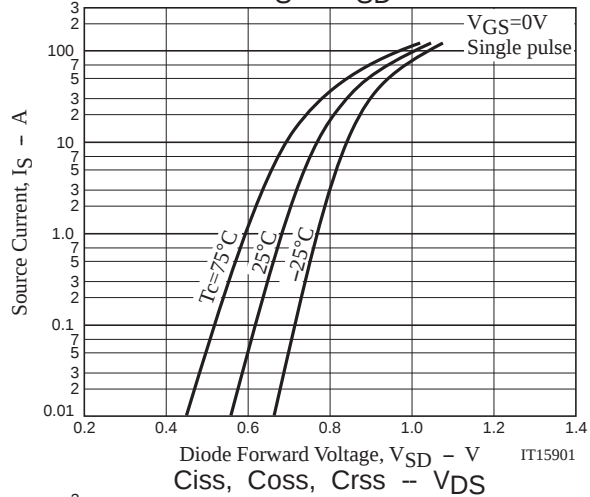
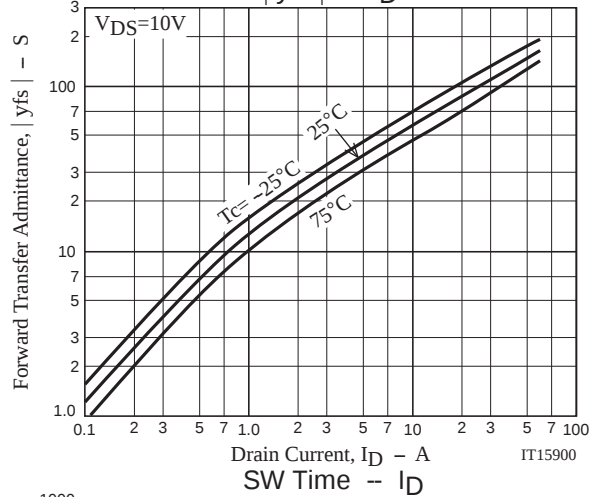
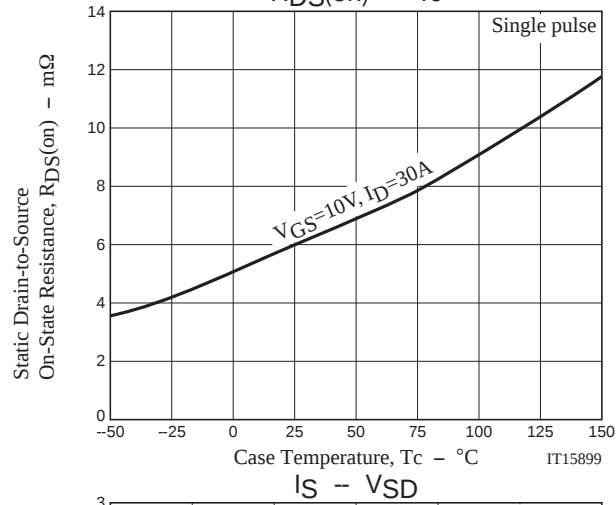
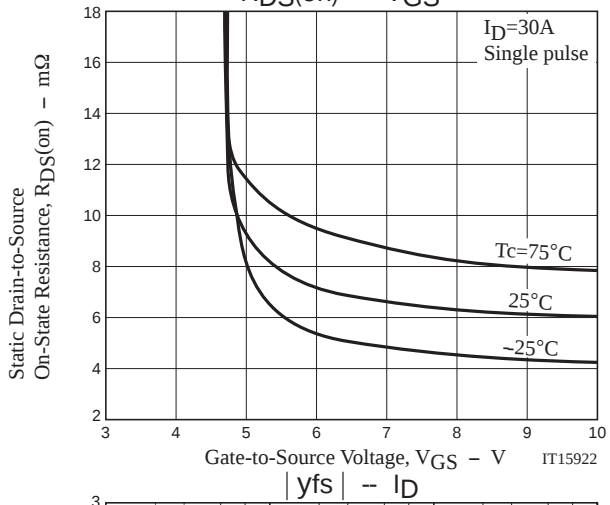
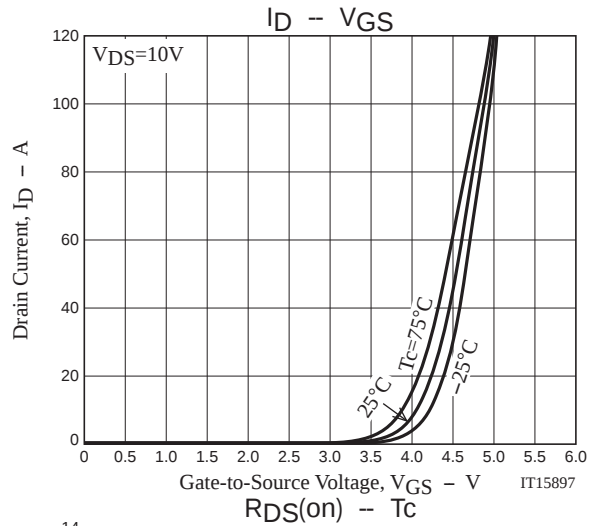
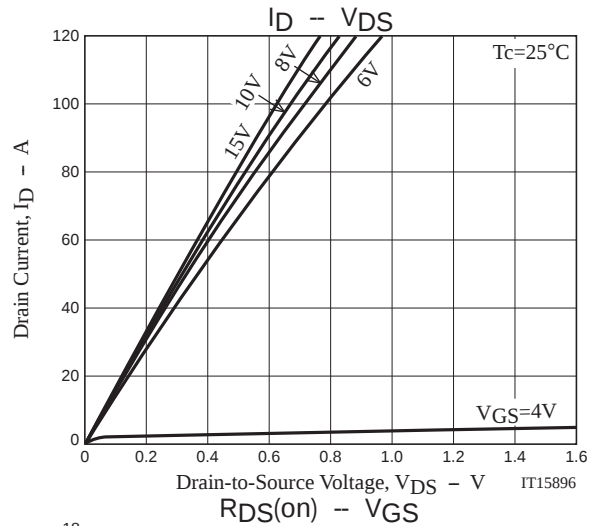
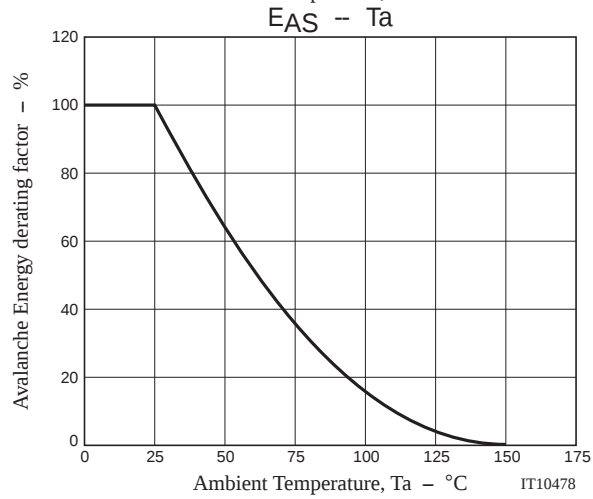
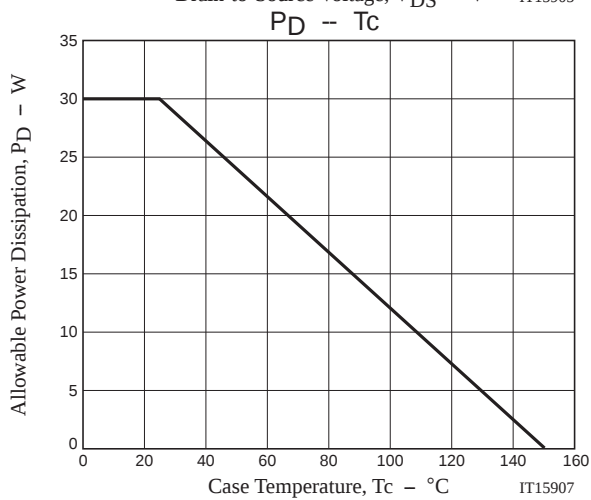
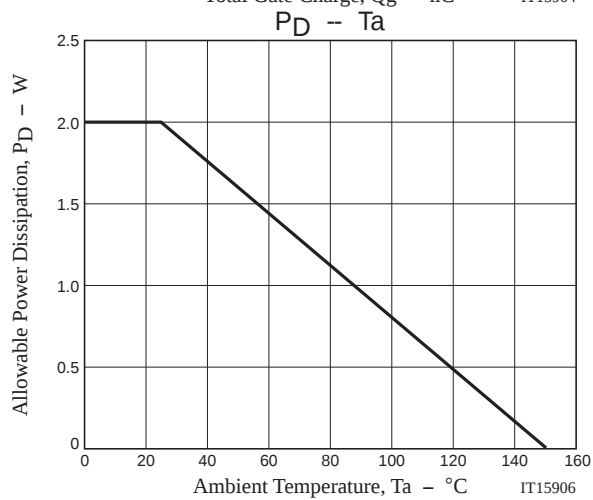
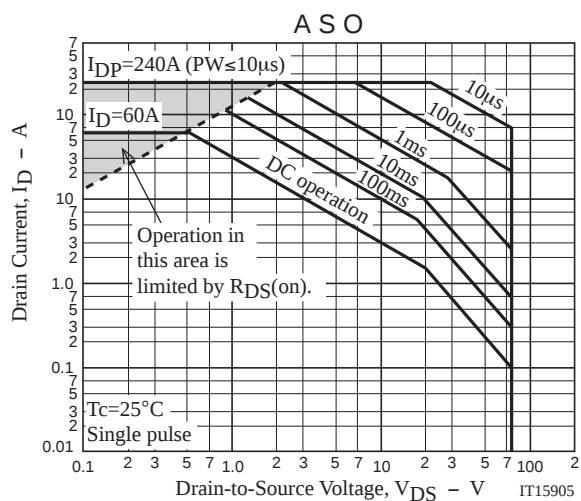
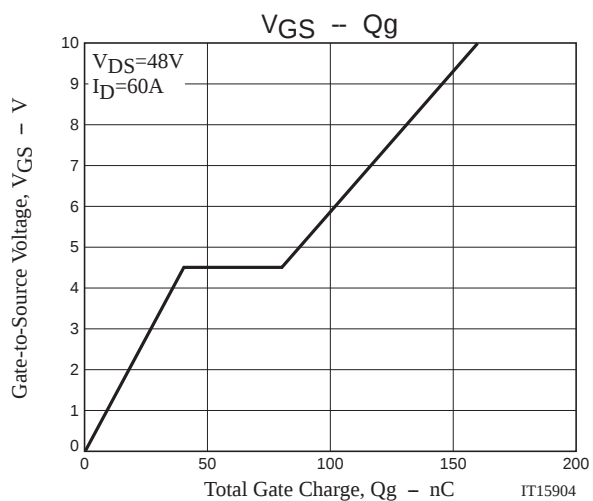


Fig.3 Reverse Recovery Time Test Circuit







Note on usage : Since the BMS4007 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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